Vishay Semiconductors

High Voltage Phase Control Thyristor, 12 A



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PRIMARY CHARACTERISTICS				
I _{T(AV)}	8 A			
V _{DRM} /V _{RRM}	800 V			
V _{TM}	1.2 V			
I _{GT}	15 mA			
TJ	-40 °C to 125 °C			
Package	TO-220AB 3L			
Circuit configuration	Single SCR			

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
Capacitive input filter $T_A = 55 \text{ °C}, T_J = 125 \text{ °C},$ common heatsink of 1 °C/W	13.5	17	A				

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	8	٨			
I _{T(RMS)}		12.5	A			
V _{DRM} /V _{RRM}		800	V			
I _{TSM}		110	А			
V _T	8 A, T _J = 25 °C	1.2	V			
dV/dt		150	V/µs			
dl/dt		100	A/µs			
TJ	Range	-40 to +125	°C			

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA
VS-12TTS08-M3	800	800	1.0

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ABSOLUTE MAXIMUM RATING	S			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T 100 °C 190° conduction half size ways	8	•
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 180° conduction, half sine wave	12.5	
Maximum peak, one-cycle,		10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	95	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T_J = 125 °C	110	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s
Maximum I-t for fusing	141	10 ms sine pulse, no voltage reapplied, T_J = 125 °C	64	
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T_J = 125 °C	640	A²√s
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V
On-state slope resistance	r _t	T ₁ = 125 °C	16.2	mΩ
Threshold voltage	V _{T(TO)}	1j = 125 0	0.87	V
Maximum reverse and direct leakage	I _{RM} /I _{DM}	$T_J = 25 \text{ °C}$ $V_B = \text{Rated } V_{BBM}/V_{DBM}$	0.05	
current		$T_{\rm J} = 125 ^{\circ}{\rm C}$	1.0	
Typical holding current	Iн	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ\text{C}$	30	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = Open$	150	V/µs
Maximum rate of rise of turned-on current	dl/dt		100	A/µs

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	vv		
Maximum peak positive gate current	+ I _{GM}		1.5	А		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	20	mA		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	15			
		Anode supply = 6 V, resistive load, T_J = 125 °C	10			
		Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	1.2			
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	1	.,		
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	0.7	V		
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Detectively	0.2			
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA		

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8	
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	3	μs
Typical turn-off time	tq	1J = 123 0	100	

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approvimate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
Mounting torque	maximum			12 (10)	(lbf · in)
Marking device			Case style TO-220AB 3L	12TT	S08

Maximum Average On-State Power Loss (W)

Maximum Average On-State Power Loss (W)

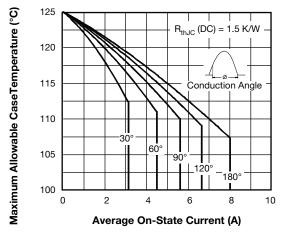


Fig. 1 - Current Ratings Characteristics

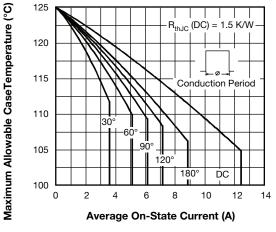


Fig. 2 - Current Ratings Characteristics

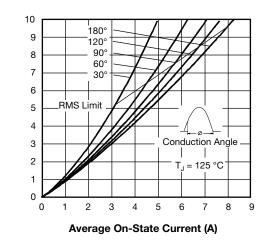


Fig. 3 - On-State Power Loss Characteristics

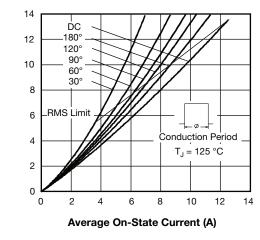


Fig. 4 - On-State Power Loss Characteristics

3

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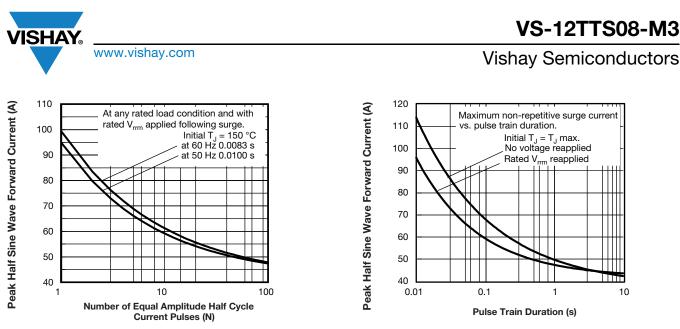
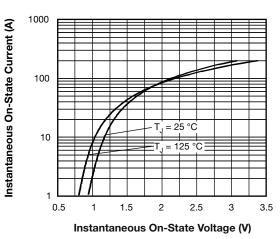


Fig. 5 - Maximum Non-Repetitive Surge Current







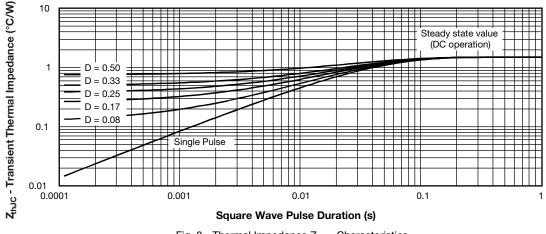


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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4

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ORDERING INFORMATION TABLE

Device code	vs-	12	т	т	s	08	-МЗ
	1	2	3	4	5	6	7
	1	- Visł	nay Sem	niconduc	ctors pro	oduct	
	2	- Cur	rent rati	ngs (12	= 12.5 A	A)	
	3	- Circ	uit conf	figuratio	n:		
		T =	single tl	hyristor			
	4	- Pac	kage:				
	_	T =	TO-220				
	5	- Тур	e of silio	con			
	_	S =	standar	rd recov	ery recti	fier	
		- Volt	age rati	ng (08 =	= 800 V)		
	7	Envi	ronmen	tal digit:			
		-M3	= halog	en-free,	RoHS-c	compliar	nt, and f

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY PACKAGING DESCRIPTION					
VS-12TTS08-M3	50	Antistatic plastic tubes				

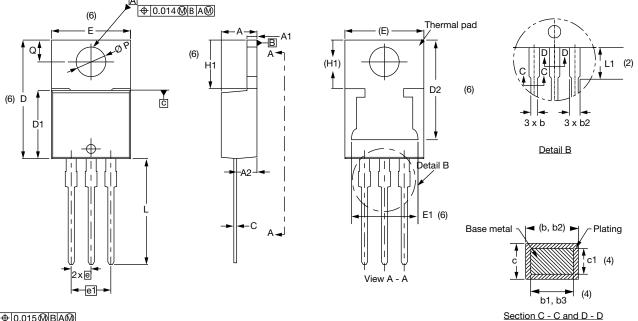
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



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TO-220AB 3L

DIMENSIONS in millimeters and inches



⊕0.015@BA@



SYMBOL	MILLIN	IETERS	INC	INCHES			
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.25	4.65	0.167	0.183			
A1	1.14	1.40	0.045	0.055			
A2	2.50	2.92	0.098	0.115			
b	0.69	1.01	0.027	0.040			
b1	0.38	0.97	0.015	0.038	4		
b2	1.20	1.73	0.047	0.068			
b3	1.14	1.73	0.045	0.068	4		
С	0.36	0.61	0.014	0.024			
c1	0.36	0.56	0.014	0.022	4		
D	14.85	15.35	0.585	0.604	3		
D1	8.38	9.02	0.330	0.355			

MILLIMETERS	INCHES

Conforms to JEDEC[®] outline TO-220AB

SYMBOL			INTOLIEO		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1

⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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1



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1